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**Etching structures in etching body using plasma comprises coupling high frequency pulsed high frequency power with etching body using high frequency alternating voltage**

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Abstract (Basic): WO 200139261 A1

NOVELTY - Etching structures in an etching body using a plasma comprises coupling a high frequency pulsed high frequency power with the etching body by means of an at least temporarily applied high frequency alternating voltage. The power is further modulated with a low frequency.

DETAILED DESCRIPTION - Preferred Features: The high frequency alternating voltage is prepared using a high frequency generator which produces a high frequency carrier signal. The high frequency pulsed high frequency power is pulsed with a frequency of 10-500, especially 50-200 kHz. The high frequency carrier signal has a frequency of 1-50, especially 13.56 MHz.

USE - For etching a silicon body.

ADVANTAGE - A higher etching rate is achieved.

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Title Terms: ETCH; STRUCTURE; ETCH; BODY; PLASMA; COMPRISE; COUPLE; HIGH; FREQUENCY; PULSE; HIGH; FREQUENCY; POWER; ETCH; BODY; HIGH; FREQUENCY; ALTERNATE; VOLTAGE

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